Microchip Technology - A3PE600-FGG256I Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	165
Number of Gates	600000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe600-fgg256i

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

I/Os Per Package[1]

ProASIC3E Devices	A3PE600		A3PE1500 [3]		A3PE3000 [3]	
Cortex-M1 Devices [2]			M1A3PE1500		M1A3PE3000	
	I/O Types					
Package	Single-Ended I/O[1]	Differential I/O Pairs	Single-Ended I/O[1]	Differential I/O Pairs	Single-Ended I/O[1]	Differential I/O Pairs
PQ208	147	65	147	65	147	65
FG256	165	79	–	–	–	–
FG324	–	–	–	–	221	110
FG484	270	135	280	139	341	168
FG676	–	–	444	222	–	–
FG896	–	–	–	–	620	310

Notes:

1. *When considering migrating your design to a lower- or higher-density device, refer to the ProASIC3E FPGA Fabric User’s Guide to ensure compliance with design and board migration requirements.*
2. *Each used differential I/O pair reduces the number of single-ended I/Os available by two.*
3. *For A3PE1500 and A3PE3000 devices, the usage of certain I/O standards is limited as follows:*
   - *– SSTL3(I) and (II): up to 40 I/Os per north or south bank*
   - *– LVPECL / GTL+ 3.3 V / GTL 3.3 V: up to 48 I/Os per north or south bank*
   - *– SSTL2(I) and (II) / GTL+ 2.5 V/ GTL 2.5 V: up to 72 I/Os per north or south bank*
4. *FG256 and FG484 are footprint-compatible packages.*
5. *When using voltage-referenced I/O standards, one I/O pin should be assigned as a voltage-referenced pin (VREF) per minibank (group of I/Os).*
6. *"G" indicates RoHS-compliant packages. Refer to the "ProASIC3E Ordering Information" on page III for the location of the "G" in the part number.*

Table 1-2 • ProASIC3E FPGAs Package Sizes Dimensions

Package	PQ208	FG256	FG324	FG484	FG676	FG896
Length × Width (mm\mm)	28 × 28	17 × 17	19 × 19	23 × 23	27 × 27	31 × 31
Nominal Area (mm^2)	784	289	361	529	729	961
Pitch (mm)	0.5	1.0	1.0	1.0	1.0	1.0
Height (mm)	3.40	1.60	1.63	2.23	2.23	2.23

ProASIC3E Device Status

ProASIC3E Devices	Status	M1 ProASIC3E Devices	Status
A3PE600	Production		
A3PE1500	Production	M1A3PE1500	Production
A3PE3000	Production	M1A3PE3000	Production

1 – ProASIC3E Device Family Overview

General Description

ProASIC3E, the third-generation family of Microsemi flash FPGAs, offers performance, density, and features beyond those of the ProASIC$^{\text{PLUS®}}$ family. Nonvolatile flash technology gives ProASIC3E devices the advantage of being a secure, low power, single-chip solution that is Instant On. ProASIC3E is reprogrammable and offers time-to-market benefits at an ASIC-level unit cost. These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

ProASIC3E devices offer 1 kbit of on-chip, programmable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on six integrated phase-locked loops (PLLs). ProASIC3E devices have up to three million system gates, supported with up to 504 kbits of true dual-port SRAM and up to 620 user I/Os.

Several ProASIC3E devices support the Cortex-M1 soft IP cores, and the ARM-Enabled devices have Microsemi ordering numbers that begin with M1A3PE.

Flash Advantages

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, flash-based ProASIC3E devices allow all functionality to be Instant On; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and field upgrades with confidence that valuable intellectual property (IP) cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The ProASIC3E family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the ProASIC3E family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/ communications, computing, and avionics markets.

Security

The nonvolatile, flash-based ProASIC3E devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. ProASIC3E devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

ProASIC3E devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of protection in the FPGA industry for programmed intellectual property and configuration data. In addition, all FlashROM data in ProASIC3E devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. The AES standard was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. ProASIC3E devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. ProASIC3E devices with AES-based security provide a high level of protection for secure, remote field updates over public networks such as the Internet, and ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of the ProASIC3E family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. The ProASIC3E family, with FlashLock and AES security, is unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. A ProASIC3E device provides the best available security for programmable logic designs.

VersaTiles

The ProASIC3E core consists of VersaTiles, which have been enhanced beyond the ProASIC$^{\underline{PLUS}®}$ core tiles. The ProASIC3E VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to Figure 1-2 for VersaTile configurations.

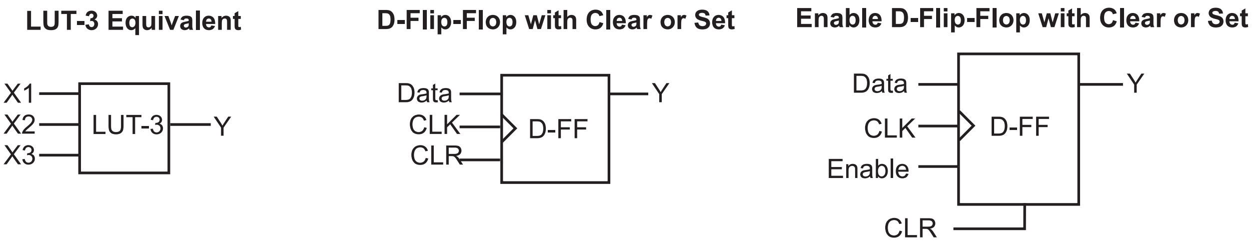


Figure 1-2 • **VersaTile Configurations**

User Nonvolatile FlashROM

ProASIC3E devices have 1 kbit of on-chip, user-accessible, nonvolatile FlashROM. The FlashROM can be used in diverse system applications:

- Internet protocol addressing (wireless or fixed)
- System calibration settings
- Device serialization and/or inventory control
- Subscription-based business models (for example, set-top boxes)
- Secure key storage for secure communications algorithms
- Asset management/tracking
- Date stamping
- Version management

The FlashROM is written using the standard ProASIC3E IEEE 1532 JTAG programming interface. The core can be individually programmed (erased and written), and on-chip AES decryption can be used selectively to securely load data over public networks, as in security keys stored in the FlashROM for a user design.

The FlashROM can be programmed via the JTAG programming interface, and its contents can be read back either through the JTAG programming interface or via direct FPGA core addressing. Note that the FlashROM can only be programmed from the JTAG interface and cannot be programmed from the internal logic array.

The FlashROM is programmed as 8 banks of 128 bits; however, reading is performed on a byte-by-byte basis using a synchronous interface. A 7-bit address from the FPGA core defines which of the 8 banks and which of the 16 bytes within that bank are being read. The three most significant bits (MSBs) of the FlashROM address determine the bank, and the four least significant bits (LSBs) of the FlashROM address define the byte.

The ProASIC3E development software solutions, Libero® System-on-Chip (SoC) and Designer, have extensive support for the FlashROM. One such feature is auto-generation of sequential programming files for applications requiring a unique serial number in each part. Another feature allows the inclusion of static data for system version control. Data for the FlashROM can be generated quickly and easily using Libero SoC and Designer software tools. Comprehensive programming file support is also included to allow for easy programming of large numbers of parts with differing FlashROM contents.

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-13 • **Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions**

				VIL		VIH		VOL	VOH	IOL[3]	IOH[3]
I/O Standard	**Drive Strength**	**Equivalent Software Default Drive Strength Option[1]**	**Slew Rate**	**Min. V**	**Max. V**	**Min. V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range	100 µA	12 mA	High	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	12	12
1.8 V LVCMOS	12 mA	12 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	12	12
1.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	12	12
3.3 V PCI	Per PCI Specification										
3.3 V PCI-X	Per PCI-X Specification										
3.3 V GTL	20 mA[2]	20 mA[2]	High	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20
2.5 V GTL	20 mA[2]	20 mA[2]	High	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20
3.3 V GTL+	35 mA	35 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	35	35
2.5 V GTL+	33 mA	33 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	33	33
HSTL (I)	8 mA	8 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	8	8
HSTL (II)	15 mA[2]	15 mA[2]	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	15	15
SSTL2 (I)	15 mA	15 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.54	VCCI – 0.62	15	15
SSTL2 (II)	18 mA	18 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.35	VCCI – 0.43	18	18
SSTL3 (I)	14 mA	14 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.7	VCCI – 1.1	14	14
SSTL3 (II)	21 mA	21 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.5	VCCI – 0.9	21	21

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *Output drive strength is below JEDEC specification.*
3. *Currents are measured at 85°C junction temperature.*
4. *Output Slew Rates can be extracted from IBIS Models, located at http://www.microsemi.com/index.php?option=com_content&id=1671&lang=en&view=article.*

Timing Characteristics

***Table 2-27* • 3.3 V LVTTL / 3.3 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.88	0.04	1.20	1.57	0.43	8.03	6.70	2.69	2.59	10.26	8.94	ns
	–1	0.56	6.71	0.04	1.02	1.33	0.36	6.83	5.70	2.29	2.20	8.73	7.60	ns
	–2	0.49.	5.89	0.03	0.90	1.17	0.32	6.00	5.01	2.01	1.93	7.67	6.67	ns
4 mA	Std.	0.66	7.88	0.04	1.20	1.57	0.43	8.03	6.70	2.69	2.59	10.26	8.94	ns
	–1	0.56	6.71	0.04	1.02	1.33	0.36	6.83	5.70	2.29	2.20	8.73	7.60	ns
	–2	0.49	5.89	0.03	0.90	1.17	0.32	6.00	5.01	2.01	1.93	7.67	6.67	ns
6 mA	Std.	0.66	5.08	0.04	1.20	1.57	0.43	5.17	4.14	3.05	3.21	7.41	6.38	ns
	–1	0.56	4.32	0.04	1.02	1.33	0.36	4.40	3.52	2.59	2.73	6.30	5.43	ns
	–2	0.49	3.79	0.03	0.90	1.17	0.32	3.86	3.09	2.28	2.40	5.53	4.76	ns
8 mA	Std.	0.66	5.08	0.04	1.20	1.57	0.43	5.17	4.14	3.05	3.21	7.41	6.38	ns
	–1	0.56	4.32	0.04	1.02	1.33	0.36	4.40	3.52	2.59	2.73	6.30	5.43	ns
	–2	0.49	3.79	0.03	0.90	1.17	0.32	3.86	3.09	2.28	2.40	5.53	4.76	ns
12 mA	Std.	0.66	3.67	0.04	1.20	1.57	0.43	3.74	2.87	3.28	3.61	5.97	5.11	ns
	–1	0.56	3.12	0.04	1.02	1.33	0.36	3.18	2.44	2.79	3.07	5.08	4.34	ns
	–2	0.49	2.74	0.03	0.90	1.17	0.32	2.79	2.14	2.45	2.70	4.46	3.81	ns
16 mA	Std.	0.66	3.46	0.04	1.20	1.57	0.43	3.53	2.61	3.33	3.72	5.76	4.84	ns
	–1	0.56	2.95	0.04	1.02	1.33	0.36	3.00	2.22	2.83	3.17	4.90	4.12	ns
	–2	0.49	2.59	0.03	0.90	1.17	0.32	2.63	1.95	2.49	2.78	4.30	3.62	ns
24 mA	Std.	0.66	3.21	0.04	1.20	1.57	0.43	3.27	2.16	3.39	4.13	5.50	4.39	ns
	–1	0.56	2.73	0.04	1.02	1.33	0.36	2.78	1.83	2.88	3.51	4.68	3.74	ns
	–2	0.49	2.39	0.03	0.90	1.17	0.32	2.44	1.61	2.53	3.08	4.11	3.28	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

***Table 2-28* • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	11.01	0.04	1.20	1.57	0.43	11.21	9.05	2.69	2.44	13.45	11.29	ns
	–1	0.56	9.36	0.04	1.02	1.33	0.36	9.54	7.70	2.29	2.08	11.44	9.60	ns
	–2	0.49	8.22	0.03	0.90	1.17	0.32	8.37	6.76	2.01	1.82	10.04	8.43	ns
4 mA	Std.	0.66	11.01	0.04	1.20	1.57	0.43	11.21	9.05	2.69	2.44	13.45	11.29	ns
	–1	0.56	9.36	0.04	1.02	1.33	0.36	9.54	7.70	2.29	2.08	11.44	9.60	ns
	–2	0.49	8.22	0.03	0.90	1.17	0.32	8.37	6.76	2.01	1.82	10.04	8.43	ns
6 mA	Std.	0.66	7.86	0.04	1.20	1.57	0.43	8.01	6.44	3.04	3.06	10.24	8.68	ns
	–1	0.56	6.69	0.04	1.02	1.33	0.36	6.81	5.48	2.58	2.61	8.71	7.38	ns
	–2	0.49	5.87	0.03	0.90	1.17	0.32	5.98	4.81	2.27	2.29	7.65	6.48	ns
8 mA	Std.	0.66	7.86	0.04	1.20	1.57	0.43	8.01	6.44	3.04	3.06	10.24	8.68	ns
	–1	0.56	6.69	0.04	1.02	1.33	0.36	6.81	5.48	2.58	2.61	8.71	7.38	ns
	–2	0.49	5.87	0.03	0.90	1.17	0.32	5.98	4.81	2.27	2.29	7.65	6.48	ns

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

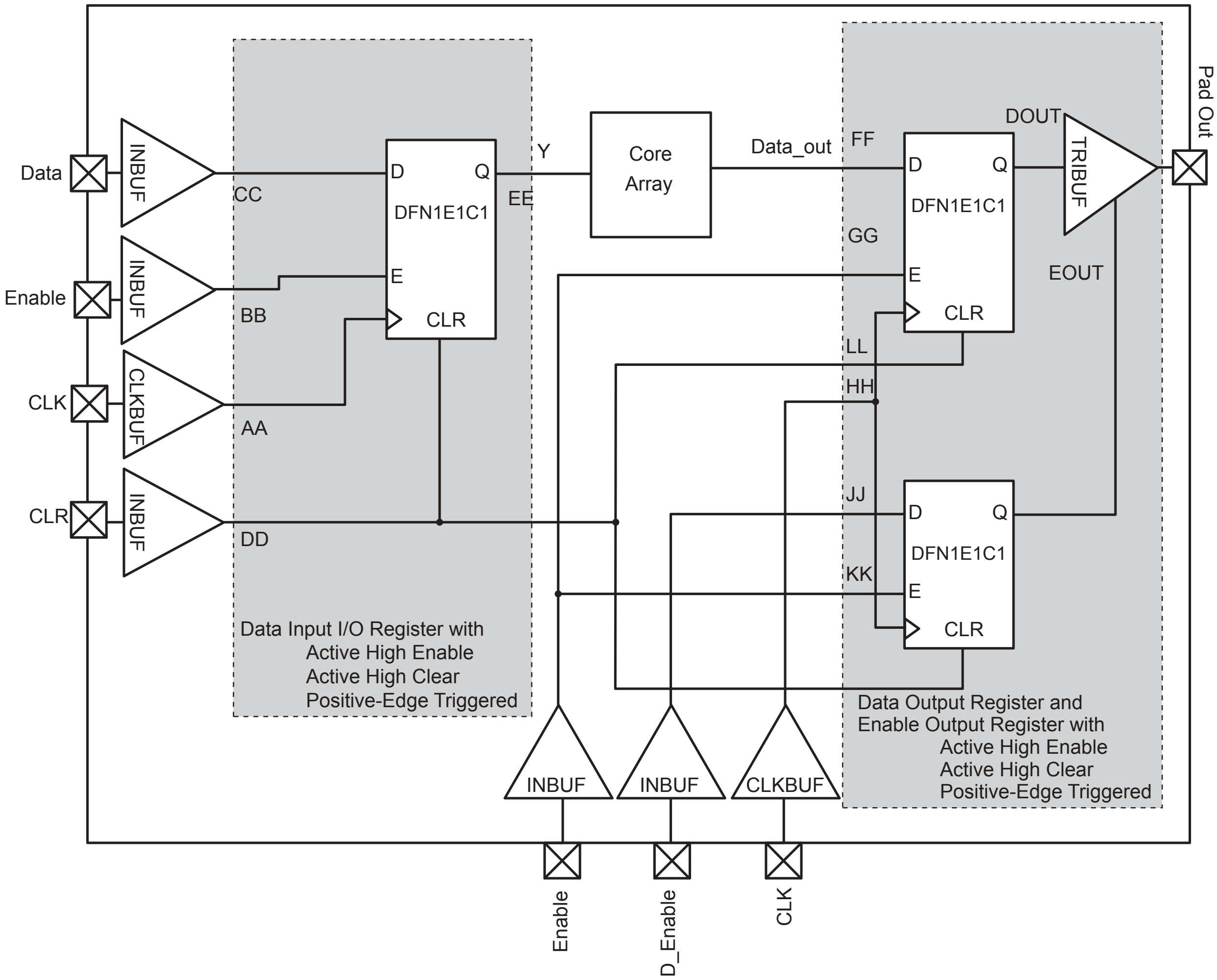


Figure 2-26 **• Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear**

Table 2-85 **• Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

*Note: *See Figure 2-26 on page 2-55 for more information.*

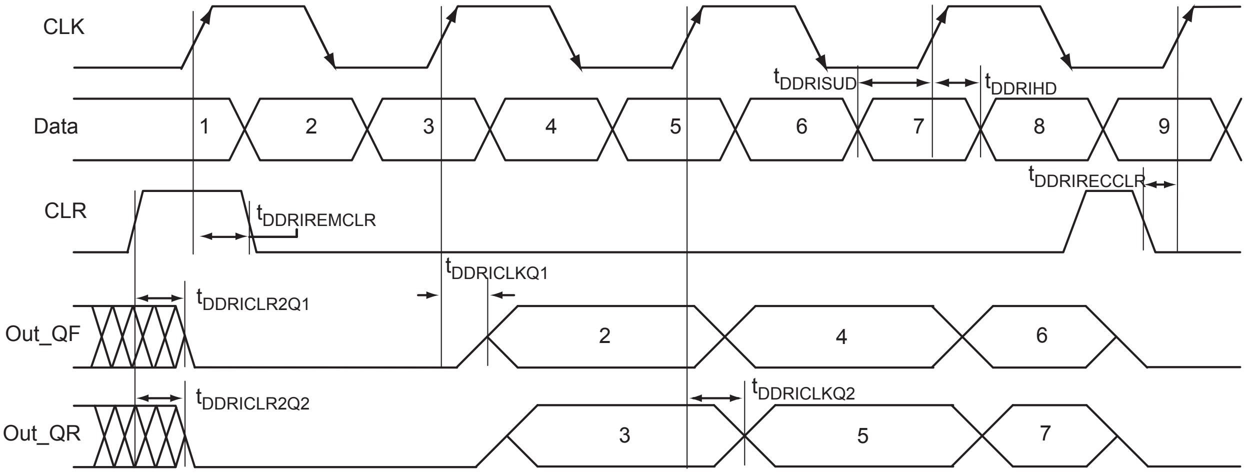


Figure 2-31 **• Input DDR Timing Diagram**

Timing Characteristics

Table 2-90 **• Input DDR Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR for Input DDR	0.39	0.44	0.52	ns
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF for Input DDR	0.27	0.31	0.37	ns
$t_{DDRISUD}$	Data Setup for Input DDR	0.28	0.32	0.38	ns
t_{DDRIHD}	Data Hold for Input DDR	0.00	0.00	0.00	ns
$t_{DDRICLR2Q1}$	Asynchronous Clear to Out Out_QR for Input DDR	0.57	0.65	0.76	ns
$t_{DDRICLR2Q2}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.46	0.53	0.62	ns
$t_{DDRIREMCLR}$	Asynchronous Clear Removal Time for Input DDR	0.00	0.00	0.00	ns
$t_{DDRIRECCLR}$	Asynchronous Clear Recovery Time for Input DDR	0.22	0.25	0.30	ns
$t_{DDRIWCLR}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.22	0.25	0.30	ns
$t_{DDRICKMPWH}$	Clock Minimum Pulse Width High for Input DDR	0.36	0.41	0.48	ns
$t_{DDRICKMPWL}$	Clock Minimum Pulse Width Low for Input DDR	0.32	0.37	0.43	ns
$F_{DDRIMAX}$	Maximum Frequency for Input DDR	1404	1232	1048	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Output DDR Module

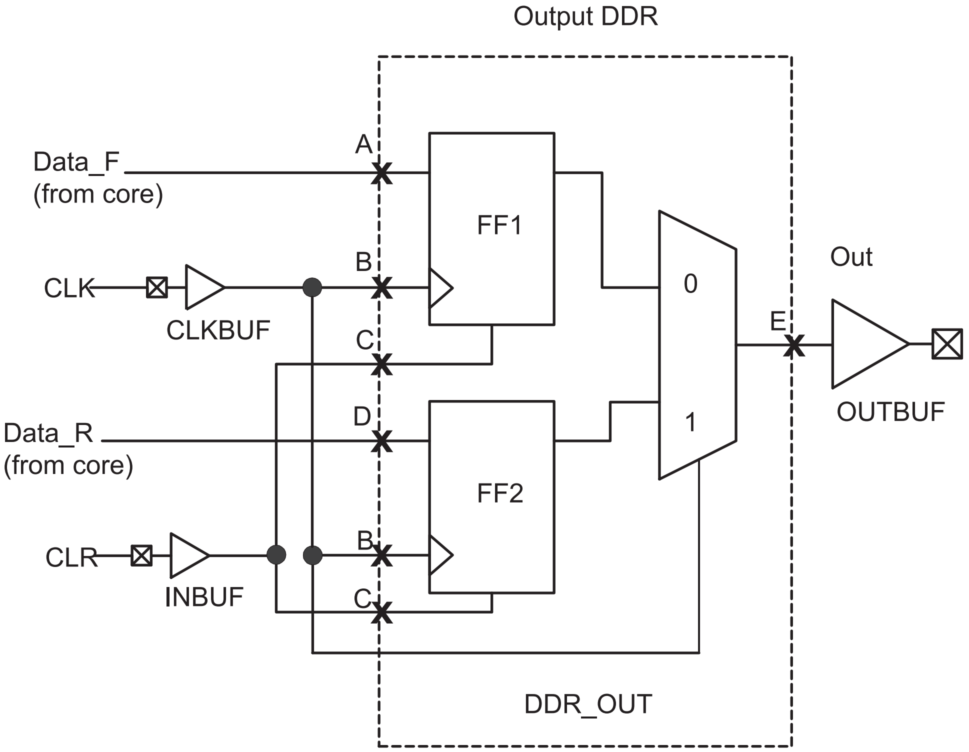


Figure 2-32 • Output DDR Timing Model

Table 2-91 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDROCLKQ}$	Clock-to-Out	B, E
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out	C, E
$t_{DDROREMCLR}$	Clear Removal	C, B
$t_{DDRORECCLR}$	Clear Recovery	C, B
$t_{DDROSUD1}$	Data Setup Data_F	A, B
$t_{DDROSUD2}$	Data Setup Data_R	D, B
$t_{DDROHD1}$	Data Hold Data_F	A, B
$t_{DDROHD2}$	Data Hold Data_R	D, B

FIFO

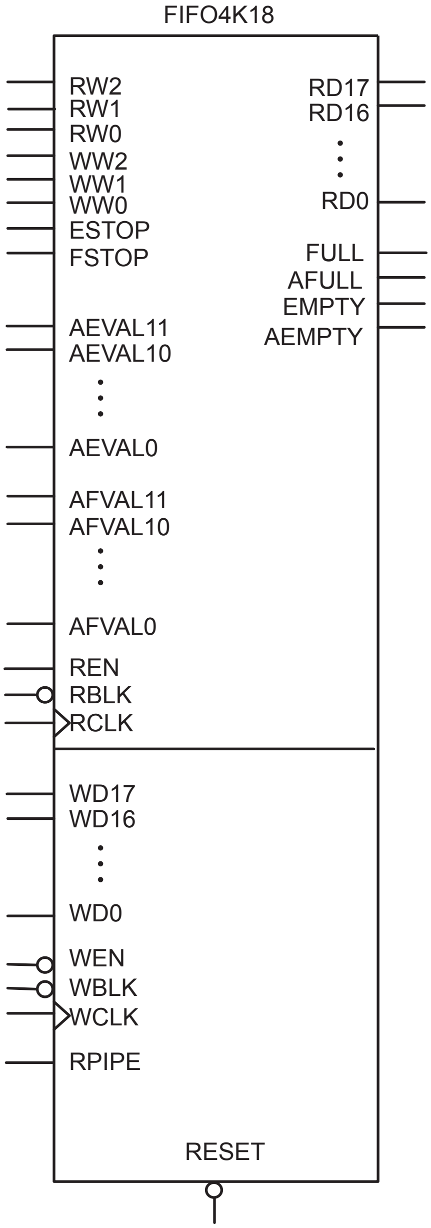


Figure 2-46 • **FIFO Model**

Special Function Pins

NC	**No Connect**

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

DC	**Do Not Connect**

This pin should not be connected to any signals on the PCB. These pins should be left unconnected.

Packaging

Semiconductor technology is constantly shrinking in size while growing in capability and functional integration. To enable next-generation silicon technologies, semiconductor packages have also evolved to provide improved performance and flexibility.

Microsemi consistently delivers packages that provide the necessary mechanical and environmental protection to ensure consistent reliability and performance. Microsemi IC packaging technology efficiently supports high-density FPGAs with large-pin-count Ball Grid Arrays (BGAs), but is also flexible enough to accommodate stringent form factor requirements for Chip Scale Packaging (CSP). In addition, Microsemi offers a variety of packages designed to meet your most demanding application and economic requirements for today's embedded and mobile systems.

Related Documents

User’s Guides

ProASIC3E FPGA Fabric User’s Guide

http://www.microsemi.com/document-portal/doc_download/130883-proasic3e-fpga-fabric-user-s-guide

Packaging

The following documents provide packaging information and device selection for low power flash devices.

Product Catalog

http://www.microsemi.com/soc/documents/ProdCat_PIB.pdf

Lists devices currently recommended for new designs and the packages available for each member of the family. Use this document or the datasheet tables to determine the best package for your design, and which package drawing to use.

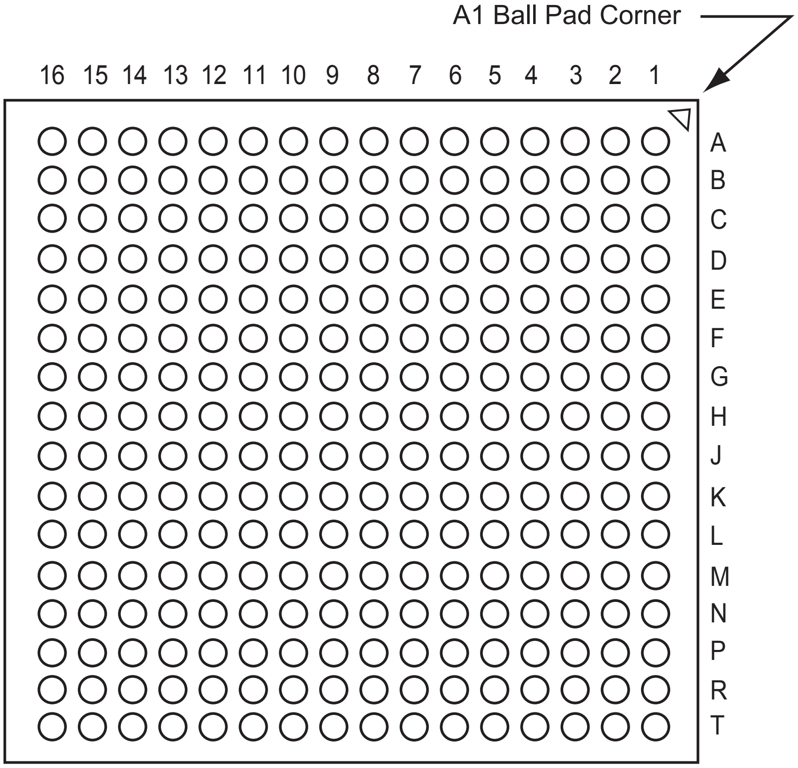
Package Mechanical Drawings

http://www.microsemi.com/document-portal/doc_download/131095-package-mechanical-drawings

This document contains the package mechanical drawings for all packages currently or previously supplied by Microsemi. Use the bookmarks to navigate to the package mechanical drawings.

Additional packaging materials: *http://www.microsemi.com/products/fpga-soc/solutions*.

FG256



Note: This is the bottom view of the package.

Note

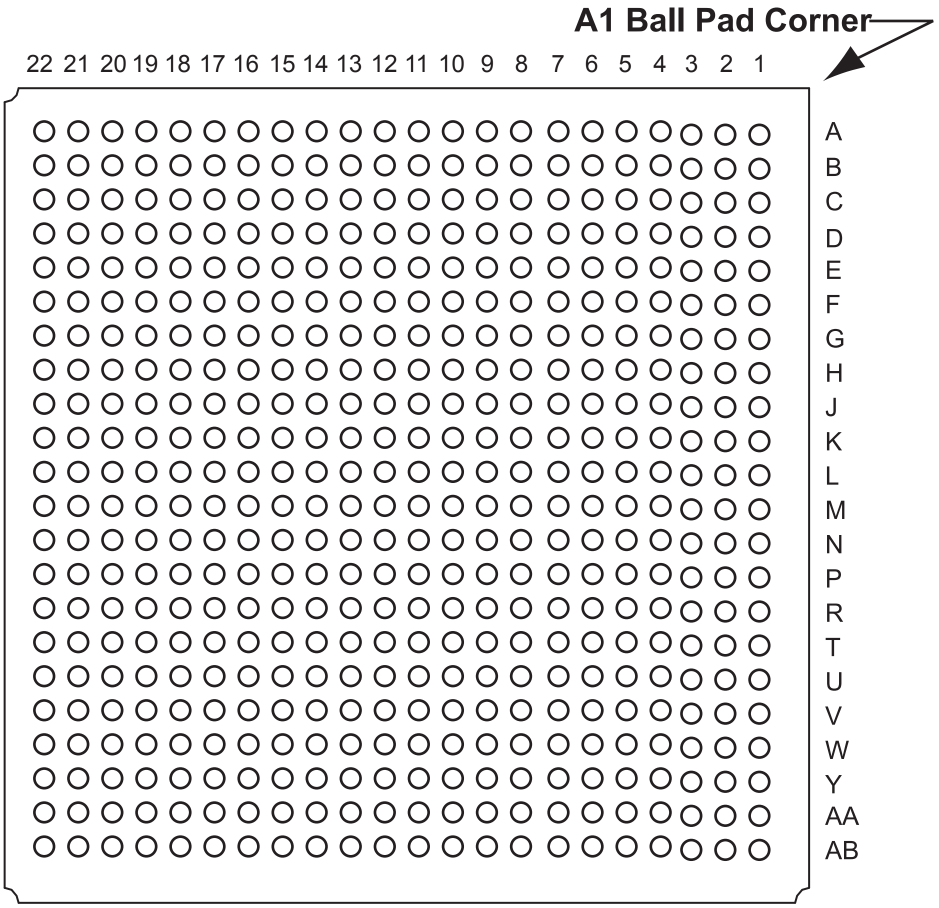
For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

FG324	
Pin Number	**A3PE3000 FBGA**
N1	IO247NDB6V1
N2	IO247PDB6V1
N3	IO251NPB6V2
N4	GEC0/IO236NDB6V0
N5	VCOMPLE
N6	IO212NDB5V2
N7	IO212PDB5V2
N8	IO192NPB4V4
N9	IO174PDB4V2
N10	IO170PDB4V2
N11	GDA2/IO154PPB4V0
N12	GDB2/IO155PPB4V0
N13	GDA1/IO153PPB3V4
N14	VCOMPLD
N15	GDB0/IO152NDB3V4
N16	GDB1/IO152PDB3V4
N17	IO138NDB3V3
N18	IO138PDB3V3
P1	IO245PDB6V1
P2	GNDQ
P3	VMV6
P4	GEC1/IO236PDB6V0
P5	VCCPLE
P6	IO214PDB5V2
P7	VCCIB5
P8	GND
P9	IO174NDB4V2
P10	IO170NDB4V2
P11	GND
P12	VCCIB4
P13	IO155NPB4V0
P14	VCCPLD
P15	VJTAG
P16	GDC0/IO151NDB3V4
P17	GDC1/IO151PDB3V4
P18	IO142PDB3V3

FG324	
Pin Number	**A3PE3000 FBGA**
R1	IO245NDB6V1
R2	VCCIB6
R3	GEA1/IO234PPB6V0
R4	IO232NDB5V4
R5	GEB2/IO232PDB5V4
R6	IO214NDB5V2
R7	IO202PDB5V1
R8	IO194PDB5V0
R9	IO186PDB4V4
R10	IO178PDB4V3
R11	IO168NSB4V1
R12	IO164PDB4V1
R13	GDC2/IO156PDB4V0
R14	TCK
R15	VPUMP
R16	TRST
R17	VCCIB3
R18	IO142NDB3V3
T1	IO241PDB6V0
T2	GEA0/IO234NPB6V0
T3	IO233NPB5V4
T4	IO231NPB5V4
T5	VMV5
T6	IO208NDB5V1
T7	IO202NDB5V1
T8	IO194NDB5V0
T9	IO186NDB4V4
T10	IO178NDB4V3
T11	IO166NPB4V1
T12	IO164NDB4V1
T13	IO156NDB4V0
T14	VMV4
T15	TDI
T16	GNDQ
T17	TDO
T18	IO146PDB3V4

FG324	
Pin Number	**A3PE3000 FBGA**
U1	IO241NDB6V0
U2	GEA2/IO233PPB5V4
U3	GEC2/IO231PPB5V4
U4	VCCIB5
U5	GNDQ
U6	IO208PDB5V1
U7	IO198PPB5V0
U8	VCCIB5
U9	IO182NPB4V3
U10	IO180NPB4V3
U11	VCCIB4
U12	IO166PPB4V1
U13	IO162PDB4V1
U14	GNDQ
U15	VCCIB4
U16	TMS
U17	VMV3
U18	IO146NDB3V4
V1	GND
V2	IO218NDB5V3
V3	IO218PDB5V3
V4	IO206NDB5V1
V5	IO206PDB5V1
V6	IO198NPB5V0
V7	GND
V8	IO190NDB4V4
V9	IO190PDB4V4
V10	IO182PPB4V3
V11	IO180PPB4V3
V12	GND
V13	IO162NDB4V1
V14	IO160NDB4V0
V15	IO160PDB4V0
V16	IO158NDB4V0
V17	IO158PDB4V0
V18	GND

FG484



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

FG484	
Pin Number	**A3PE1500 Function**
A1	GND
A2	GND
A3	VCCIB0
A4	IO05NDB0V0
A5	IO05PDB0V0
A6	IO11NDB0V1
A7	IO11PDB0V1
A8	IO15PDB0V1
A9	IO17PDB0V2
A10	IO27NDB0V3
A11	IO27PDB0V3
A12	IO32PDB1V0
A13	IO43PDB1V1
A14	IO47NDB1V1
A15	IO47PDB1V1
A16	IO51NDB1V2
A17	IO51PDB1V2
A18	IO54NDB1V3
A19	NC
A20	VCCIB1
A21	GND
A22	GND
AA1	GND
AA2	VCCIB6
AA3	NC
AA4	IO161PDB5V3
AA5	IO155NDB5V2
AA6	IO155PDB5V2
AA7	IO154NDB5V2
AA8	IO154PDB5V2
AA9	IO143PDB5V1
AA10	IO143NDB5V1
AA11	IO131PPB4V2
AA12	IO129NDB4V2
AA13	IO129PDB4V2
AA14	NC
AA15	NC
AA16	IO117NDB4V0
AA17	IO117PDB4V0
AA18	IO115NDB4V0
AA19	IO115PDB4V0
AA20	NC
AA21	VCCIB3
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB5
AB4	IO159NDB5V3
AB5	IO159PDB5V3
AB6	IO149NDB5V1
AB7	IO149PDB5V1
AB8	IO138NDB5V0
AB9	IO138PDB5V0
AB10	NC
AB11	NC
AB12	IO127NDB4V2
AB13	IO127PDB4V2
AB14	IO125NDB4V1
AB15	IO125PDB4V1
AB16	IO122NDB4V1
AB17	IO122PDB4V1
AB18	NC
AB19	NC
AB20	VCCIB4
AB21	GND
AB22	GND
B1	GND
B2	VCCIB7
B3	NC
B4	IO03NDB0V0
B5	IO03PDB0V0
B6	IO10NDB0V1
B7	IO10PDB0V1
B8	IO15NDB0V1
B9	IO17NDB0V2
B10	IO20PDB0V2
B11	IO29PDB0V3
B12	IO32NDB1V0
B13	IO43NDB1V1
B14	NC
B15	NC
B16	IO53NDB1V2
B17	IO53PDB1V2
B18	IO54PDB1V3
B19	NC
B20	NC
B21	VCCIB2
B22	GND
C1	VCCIB7
C2	NC
C3	NC
C4	NC
C5	GND
C6	IO07NDB0V0
C7	IO07PDB0V0
C8	VCC
C9	VCC
C10	IO20NDB0V2
C11	IO29NDB0V3
C12	NC
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC

FG676	
Pin Number	**A3PE1500 Function**
G13	IO21NDB0V2
G14	IO27PDB0V3
G15	IO35NDB1V0
G16	IO39PDB1V0
G17	IO51NDB1V2
G18	IO53NDB1V2
G19	VCCIB1
G20	GBA2/IO58PPB2V0
G21	GNDQ
G22	IO64NDB2V1
G23	IO64PDB2V1
G24	IO72PDB2V2
G25	IO72NDB2V2
G26	IO78PDB2V2
H1	IO208NDB7V2
H2	IO208PDB7V2
H3	IO209NDB7V2
H4	IO209PDB7V2
H5	IO219NDB7V3
H6	GAC2/IO219PDB7V3
H7	VCCIB7
H8	VCC
H9	VCCIB0
H10	VCCIB0
H11	VCCIB0
H12	VCCIB0
H13	VCCIB0
H14	VCCIB1
H15	VCCIB1
H16	VCCIB1
H17	VCCIB1
H18	VCCIB1
H19	VCC
H20	VCC
H21	IO58NPB2V0
H22	IO70PDB2V1
H23	IO69PDB2V1
H24	IO76PDB2V2
H25	IO76NDB2V2
H26	IO78NDB2V2
J1	IO197NDB7V0
J2	IO197PDB7V0
J3	VMV7
J4	IO215NDB7V3
J5	IO215PDB7V3
J6	IO214PDB7V3
J7	IO214NDB7V3
J8	VCCIB7
J9	VCC
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	VCC
J15	VCC
J16	VCC
J17	VCC
J18	VCC
J19	VCCIB2
J20	IO62PDB2V0
J21	IO62NDB2V0
J22	IO70NDB2V1
J23	IO69NDB2V1
J24	VMV2
J25	IO80PDB2V3
J26	IO80NDB2V3
K1	IO195PDB7V0
K2	IO199NDB7V1
K3	IO199PDB7V1
K4	IO205NDB7V1
K5	IO205PDB7V1
K6	IO217PDB7V3
K7	IO217NDB7V3
K8	VCCIB7
K9	VCC
K10	GND
K11	GND
K12	GND
K13	GND
K14	GND
K15	GND
K16	GND
K17	GND
K18	VCC
K19	VCCIB2
K20	IO65PDB2V1
K21	IO65NDB2V1
K22	IO74PDB2V2
K23	IO74NDB2V2
K24	IO75PDB2V2
K25	IO75NDB2V2
K26	IO84PDB2V3
L1	IO195NDB7V0
L2	IO198PPB7V0
L3	GNDQ
L4	IO201PDB7V1
L5	IO201NDB7V1
L6	IO210NDB7V2
L7	IO210PDB7V2
L8	VCCIB7
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	GND
L15	GND
L16	GND

FG676	
Pin Number	**A3PE1500 Function**
R21	IO89NDB3V0
R22	GCB2/IO89PDB3V0
R23	IO90NDB3V0
R24	GCC2/IO90PDB3V0
R25	IO91PDB3V0
R26	IO91NDB3V0
T1	IO186PDB6V2
T2	IO185NDB6V2
T3	GNDQ
T4	IO180PDB6V1
T5	IO180NDB6V1
T6	IO188NDB6V2
T7	GFB2/IO188PDB6V2
T8	VCCIB6
T9	VCC
T10	GND
T11	GND
T12	GND
T13	GND
T14	GND
T15	GND
T16	GND
T17	GND
T18	VCC
T19	VCCIB3
T20	IO99PDB3V1
T21	IO99NDB3V1
T22	IO97PDB3V1
T23	IO97NDB3V1
T24	GNDQ
T25	IO93PPB3V0
T26	NC
U1	IO186NDB6V2
U2	IO184NDB6V2
U3	IO184PDB6V2
U4	IO182NDB6V1

FG676	
Pin Number	**A3PE1500 Function**
U5	IO182PDB6V1
U6	IO178PDB6V1
U7	IO178NDB6V1
U8	VCCIB6
U9	VCC
U10	GND
U11	GND
U12	GND
U13	GND
U14	GND
U15	GND
U16	GND
U17	GND
U18	VCC
U19	VCCIB3
U20	NC
U21	IO101NDB3V1
U22	IO101PDB3V1
U23	IO92NDB3V0
U24	IO92PDB3V0
U25	IO95PDB3V1
U26	IO93NPB3V0
V1	IO183PDB6V2
V2	IO183NDB6V2
V3	VMV6
V4	IO181PDB6V1
V5	IO181NDB6V1
V6	IO176PDB6V1
V7	IO176NDB6V1
V8	VCCIB6
V9	VCC
V10	VCC
V11	VCC
V12	VCC
V13	VCC
V14	VCC

FG676	
Pin Number	**A3PE1500 Function**
V15	VCC
V16	VCC
V17	VCC
V18	VCC
V19	VCCIB3
V20	IO107PDB3V2
V21	IO107NDB3V2
V22	IO103NDB3V2
V23	IO103PDB3V2
V24	VMV3
V25	IO95NDB3V1
V26	IO94PDB3V0
W1	IO179NDB6V1
W2	IO179PDB6V1
W3	IO177NDB6V1
W4	IO177PDB6V1
W5	IO172PDB6V0
W6	IO172NDB6V0
W7	VCC
W8	VCC
W9	VCCIB5
W10	VCCIB5
W11	VCCIB5
W12	VCCIB5
W13	VCCIB5
W14	VCCIB4
W15	VCCIB4
W16	VCCIB4
W17	VCCIB4
W18	VCCIB4
W19	VCC
W20	VCCIB3
W21	GDB0/IO109NDB3V2
W22	GDB1/IO109PDB3V2
W23	IO105NDB3V2
W24	IO105PDB3V2

FG896

Pin Number	A3PE3000 Function
M23	IO104PPB2V2
M24	IO102PDB2V2
M25	IO102NDB2V2
M26	IO95PDB2V1
M27	IO97NDB2V1
M28	IO101NDB2V2
M29	IO103NDB2V2
M30	IO119PDB3V0
N1	IO276PDB7V0
N2	IO278PDB7V0
N3	IO280PDB7V0
N4	IO284PDB7V1
N5	IO279PDB7V0
N6	IO285NDB7V1
N7	IO287NDB7V1
N8	IO281NDB7V0
N9	IO281PDB7V0
N10	VCCIB7
N11	VCC
N12	GND
N13	GND
N14	GND
N15	GND
N16	GND
N17	GND
N18	GND
N19	GND
N20	VCC
N21	VCCIB2
N22	IO106NDB2V3
N23	IO106PDB2V3
N24	IO108PDB2V3
N25	IO108NDB2V3
N26	IO95NDB2V1
N27	IO99NDB2V2
N28	IO99PDB2V2
N29	IO107PDB2V3
N30	IO107NDB2V3
P1	IO276NDB7V0
P2	IO278NDB7V0
P3	IO280NDB7V0
P4	IO284NDB7V1
P5	IO279NDB7V0
P6	GFC1/IO275PDB7V0
P7	GFC0/IO275NDB7V0
P8	IO277PDB7V0
P9	IO277NDB7V0
P10	VCCIB7
P11	VCC
P12	GND
P13	GND
P14	GND
P15	GND
P16	GND
P17	GND
P18	GND
P19	GND
P20	VCC
P21	VCCIB2
P22	GCC1/IO112PDB2V3
P23	IO110PDB2V3
P24	IO110NDB2V3
P25	IO109PPB2V3
P26	IO111NPB2V3
P27	IO105PDB2V2
P28	IO105NDB2V2
P29	GCC2/IO117PDB3V0
P30	IO117NDB3V0
R1	GFC2/IO270PDB6V4
R2	GFB1/IO274PPB7V0
R3	VCOMPLF
R4	GFA0/IO273NDB6V4
R5	GFB0/IO274NPB7V0
R6	IO271NDB6V4
R7	GFB2/IO271PDB6V4
R8	IO269PDB6V4
R9	IO269NDB6V4
R10	VCCIB7
R11	VCC
R12	GND
R13	GND
R14	GND
R15	GND
R16	GND
R17	GND
R18	GND
R19	GND
R20	VCC
R21	VCCIB2
R22	GCC0/IO112NDB2V3
R23	GCB2/IO116PDB3V0
R24	IO118PDB3V0
R25	IO111PPB2V3
R26	IO122PPB3V1
R27	GCA0/IO114NPB3V0
R28	VCOMPLC
R29	GCB1/IO113PPB2V3
R30	IO115NPB3V0
T1	IO270NDB6V4
T2	VCCPLF
T3	GFA2/IO272PPB6V4
T4	GFA1/IO273PDB6V4
T5	IO272NPB6V4
T6	IO267NDB6V4
T7	IO267PDB6V4
T8	IO265PDB6V3
T9	IO263PDB6V3
T10	VCCIB6

Revision	Changes	Page
Revision 10 (March 2012)	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 34669).	I, 1-1
	The Y security option and Licensed DPA Logo were added to the "ProASIC3E Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 34727).	III
	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOOe devices via an IEEE 1532 JTAG interface" (SAR 34689).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 34699).	1-6
	VCCPLL in Table 2-2 • Recommended Operating Conditions [1] was corrected from "1.4 to 1.6 V" to "1.425 to 1.575 V" (SAR 33851). The T_J symbol was added to the table and notes regarding T_A and T_J were removed. The second of two parameters in the VCCI and VMV row, called "3.3 V DC supply voltage," was corrected to "3.0 V DC supply voltage" (SAR 37227).	2-2
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—P_{CLOCK}" section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide* (SAR 34735).	2-9
	t_{DOUT} was corrected to t_{DIN} in Figure 2-3 • Input Buffer Timing Model and Delays (example) (SAR 37109).	2-13
	The typo related to the values for 3.3 V LVCMOS Wide Range in Table 2-17 • Summary of I/O Timing Characteristics—Software Default Settings was corrected (SAR 37227).	2-19
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section and "3.3 V LVCMOS Wide Range" section and tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is ±100 µA. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 34763).	2-18, 2-27

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Microsemi Corporate Headquarters
One Enterprise, Aliso Viejo,
CA 92656 USA

Within the USA: +1 (800) 713-4113
Outside the USA: +1 (949) 380-6100
Sales: +1 (949) 380-6136
Fax: +1 (949) 215-4996

E-mail: sales.support@microsemi.com

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